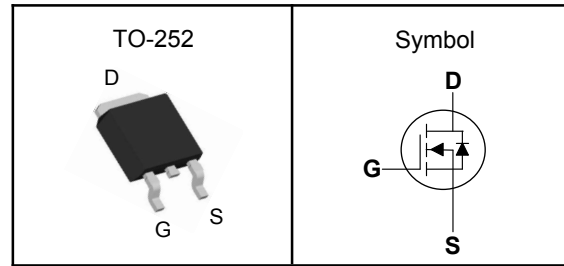


N-Channel Enhancement Mode MOSFET
Features

- Fast switching speed
- Reliable and Rugged
- ROHS Compliant
- 100% UIS and Rg Tested

Applications

- Power Management in Desktop Computer
- DC/DC Converters

Pin Description


V_{DSS}	200	V
$R_{DS(ON)-Typ}$	600	m Ω
I_D	4.5	A

Absolute Maximum Ratings($T_C=25^{\circ}C$, Unless Otherwise Noted)

Symbol	Parameter	N-Channel	Unit
V_{DSS}	Drain-Source Voltage	200	V
V_{GSS}	Gate-Source Voltage	± 30	V
T_J	Maximum Junction Temperature	-55 to 150	$^{\circ}C$
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
E_{AS}	Single Pulse Avalanche Energy ³	20	mJ
$I_{DM}^{①}$	Pulse Drain Current Tested	9	A
I_D	Continuous Drain Current	4.5	A
P_D	Maximum Power Dissipation	36	W

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ (Max)	50	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	3.5	$^{\circ}C/W$

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150 $^{\circ}C$.

Note ③ : Surface Mounted on 1in² FR-4 board with 1oz.



N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_J=25°C, Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250mA	200	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =200V, V _{GS} =0V	---	---	1	uA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	---	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±30V, V _{DS} =0V	---	---	±100	nA
R _{DS(on)}	Drain-Source On-state Resistance	V _{GS} =10V, I _D =2.9A	---	600	700	mΩ
Dynamic Characteristics ^⑤						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, Freq.=1MHz	---	230	---	pF
C _{oss}	Output Capacitance		---	25	---	
C _{rss}	Reverse Transfer Capacitance		---	9	---	
T _{d(on)}	Turn-on Delay Time	V _{DD} =100V, V _{GS} =10V, R _G =25Ω, I _D =4A	---	9	---	nS
T _r	Turn-on Rise Time		---	16	---	
T _{d(off)}	Turn-off Delay Time		---	15	---	
T _f	Turn-off Fall Time		---	13	---	
Q _g	Total Gate Charge	V _{DD} =160V, V _{GS} =10V, I _D =4A	---	6.5	---	nC
Q _{gs}	Gate-Source Charge		---	1.3	---	
Q _{gd}	Gate-Drain Charge		---	3.2	---	
Source-Drain Characteristics (T _J =25°C)						
V _{SD}	Diode Forward Voltage ₂	V _{GS} =0V, I _S =1A, T _J =25°C	---	0.7	1.2	V
t _{rr}	Reverse Recovery Time	I _F =2A, V _R =0V di/dt=100A/μs, T _J =25°C	---	120	---	nS
Q _{rr}	Reverse Recovery Charge		---	500	---	nC

Note ④ : Pulse test (pulse width≤300us, duty cycle≤2%).

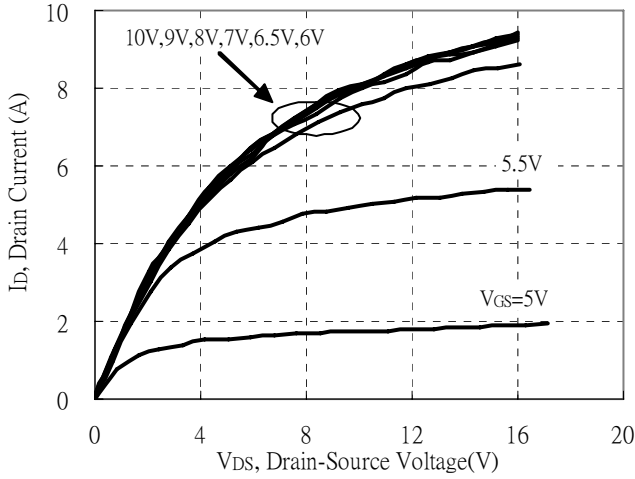
Note ⑤ : Guaranteed by design, not subject to production testing.



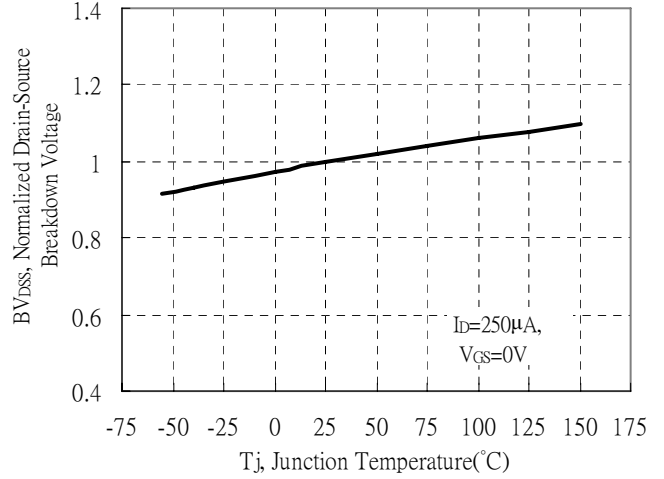
N-Channel Enhancement Mode MOSFET

Typical Characteristics

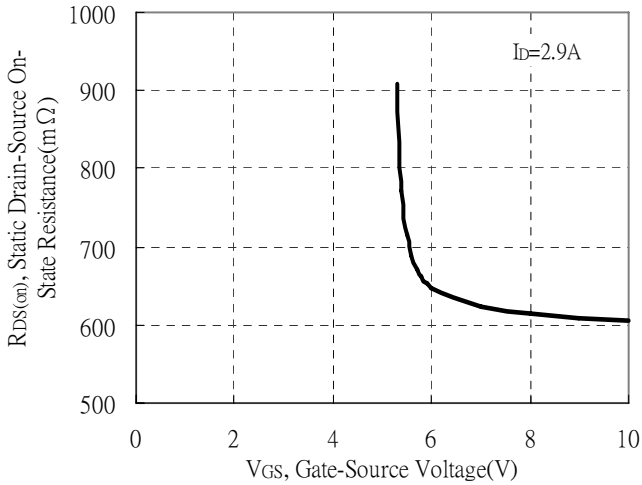
Typical Output Characteristics



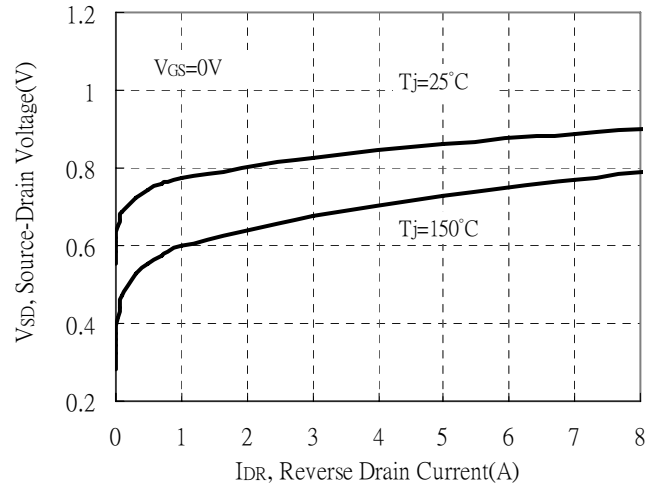
Brekdown Voltage vs Ambient Temperature



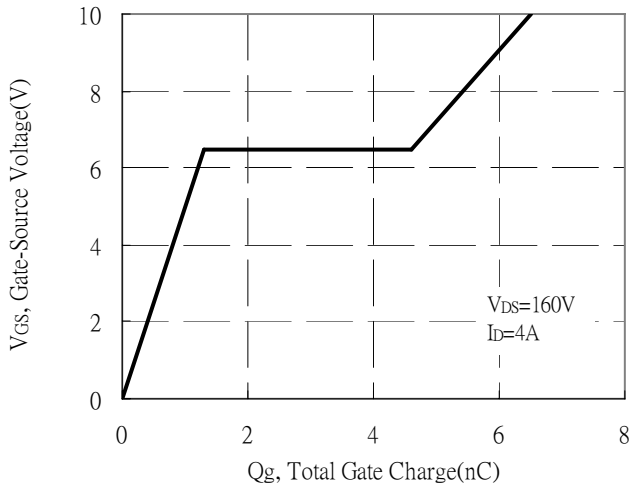
Static Drain-Source On-State Resistance vs Gate-Source Voltage



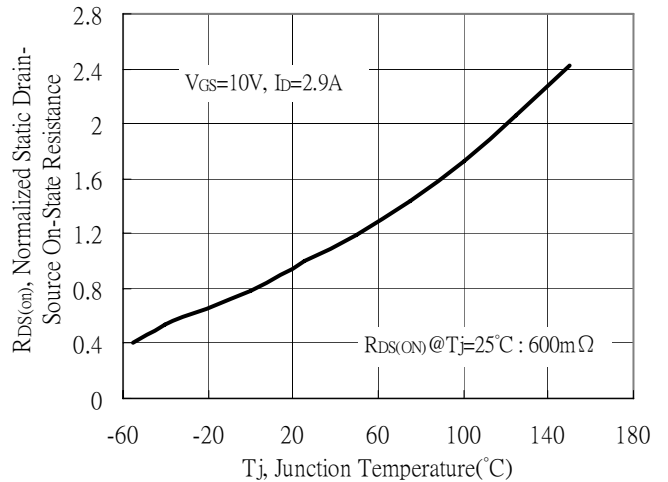
Reverse Drain Current vs Source-Drain Voltage



Gate Charge Characteristics

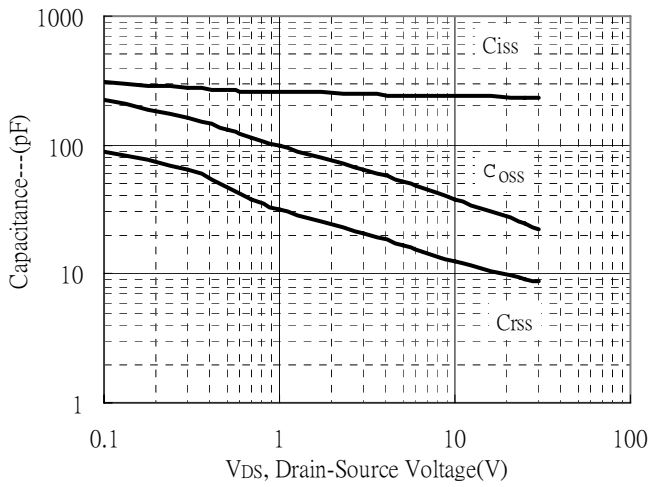


Drain-Source On-State Resistance vs Junction Temperature

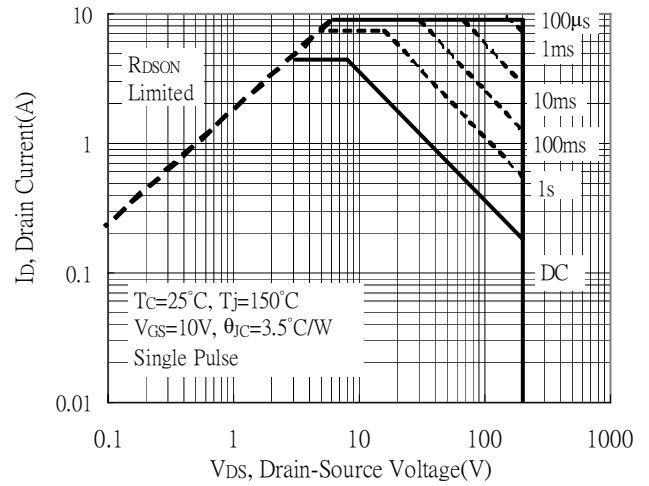


N-Channel Enhancement Mode MOSFET

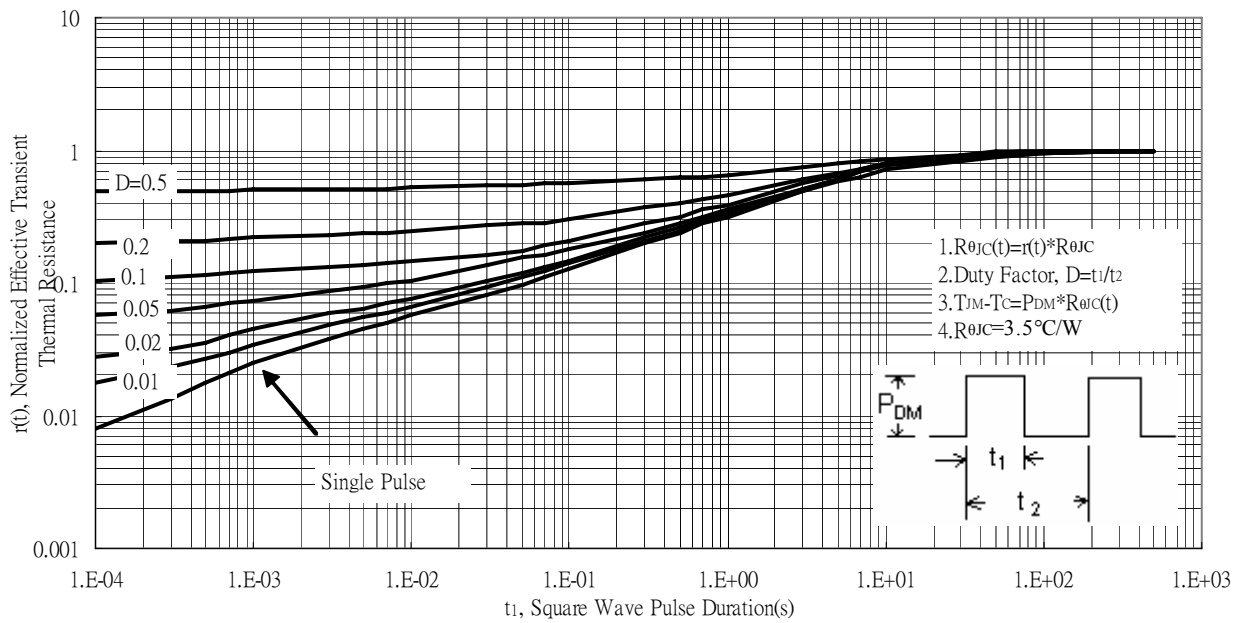
Capacitance vs Drain-to-Source Voltage

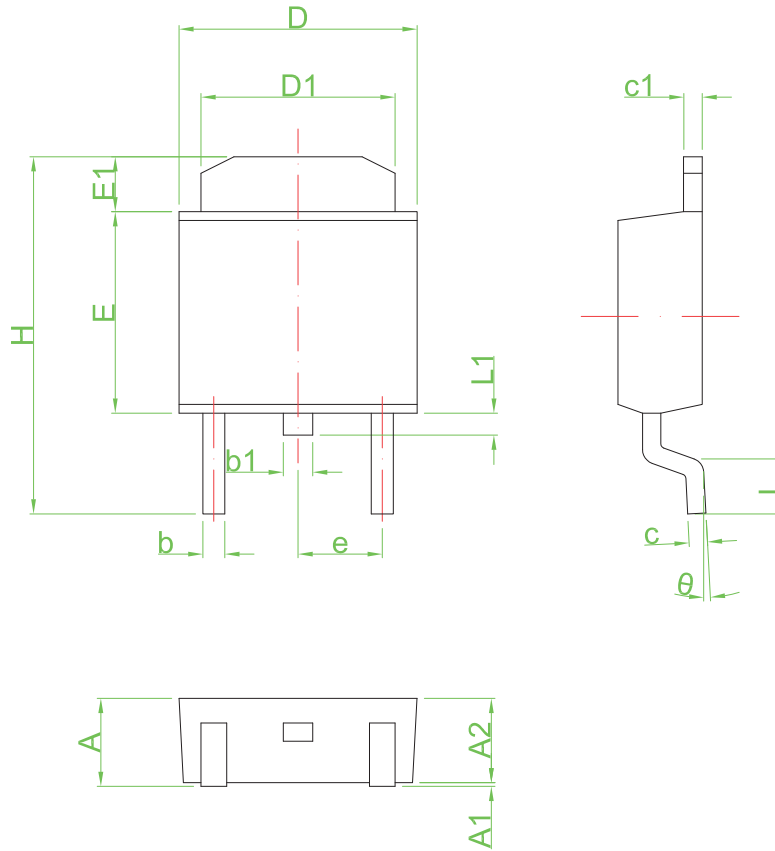


Maximum Safe Operating Area



Transient Thermal Response Curves



N-Channel Enhancement Mode MOSFET
TO-252 Package Outline Dimensions


Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	2.25	2.65	0.089	0.104
A1	0.00	0.15	0.000	0.006
A2	2.20	2.40	0.087	0.094
b	0.50	0.70	0.020	0.028
b1	0.70	0.90	0.028	0.035
c	0.46	0.66	0.018	0.026
c1	0.46	0.66	0.018	0.026
D	6.30	6.70	0.248	0.264
D1	5.20	5.40	0.205	0.213
E	5.30	5.70	0.209	0.224
E1	1.40	1.60	0.055	0.063
H	9.40	9.90	0.370	0.390
e	2.30 TYP		0.09 TYP	
L	1.40	1.77	0.055	0.070
L1	0.50	0.70	0.020	0.028
theta	0°	8°	0°	8°